

Schottky barrier diode

RB717F

●Applications

General purpose detection

High speed switching

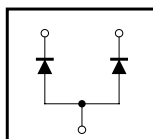
●Features

- 1) Small surface mounting type. (UMD3)
- 2) Low reverse current and low forward voltage.
- 3) High reliability.

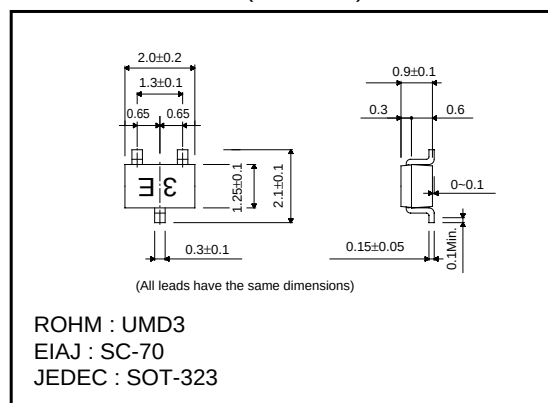
●Construction

Silicon epitaxial planar

●Circuit



●External dimensions (Units : mm)



●Absolute maximum ratings (Ta = 25°C)

Parameter	Symbol	Limits	Unit
Peak reverse voltage	V_{RM}	40	V
DC reverse voltage	V_R	40	V
Mean rectifying current	I_o	30	mA
Peak forward surge current *	I_{FSM}	200	mA
Junction temperature	T_j	125	°C
Storage temperature	T_{stg}	-40~+125	°C

*60 Hz for 1

●Electrical characteristics (Ta = 25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V_F	—	—	0.37	V	$I_F=1mA$
Reverse current	I_R	—	—	1	μA	$V_R=10V$
Capacitance between terminals	C_T	—	2.0	—	pF	$V_R=1V, f=1MHz$

Note) ESD sensitive product handling required.

Diodes

● Electrical characteristic curves ($T_a = 25^\circ\text{C}$)